Freeform Search

Database:	US Pre-Grant Publication Full-Text Database US Patents Full-Text Database US OCR Full-Text Database EPO Abstracts Database JPO Abstracts Database Derwent World Patents Index IBM Technical Disclosure Bulletins							
Term:	L6 and gate							
Display:	Documents in Display Format: - Starting with Number 1	<u> </u>						
Generate:	Generate: C Hit List • Hit Count C Side by Side C Image Search Clear Interrupt							
	Search History							

DATE: Tuesday, April 12, 2005 Printable Copy Create Case

Set Name side by side	Query	<u>Hit</u> <u>Count</u>	Set Name result set
DB=P	GPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD; PLUR=YES; OP=OR		
<u>L7</u>	L6 and gate	387	<u>L7</u>
<u>L6</u>	L4 and nm	421	<u>L6</u>
<u>L5</u>	L4 and nm	421	<u>L5</u>
<u>L4</u>	L3 and (nitride with (thin or thick or thickness))	647	<u>L4</u>
<u>L3</u>	((ultra-small or minute or small\$2 or nano-scale) with grain\$1) and polysilicon and nitride	1146	<u>L3</u>
<u>L2</u>	L1 and polysilicon	73	<u>L2</u>
<u>L1</u>	(grain adj size) with nitride	1676	<u>L1</u>

END OF SEARCH HISTORY

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
1	IS&R	L1		lysilicon").PN.	USOCR	2005/04/1 2 08:40	
2	BRS	 L2	536	((grain adj size) with polysilicon)	USPAT	2005/04/1 2 08:41	
3	BRS	L3	1/45	L2 and gate and nitride	USPAT	2005/04/1 2 08:41	